

GRF2051

Linear, Ultra-Low Noise Amplifier; 1.7 – 2.7 GHz

Package: 12-Pin QFN



Features

- 1700-2700 MHz with Single Tune
- Reference Frequency/Bias Condition: 1900 MHz; 5V/55 mA
- Evaluation Board Gain: 19.0 dB
- Evaluation Board NF: 0.35 dB
- De-embedded NF: 0.25 dB
- IIP3: +20.0 dBm
- IP1dB: +3.0 dBm
- Flexible Vdd: 3.0 6.0 volts
- Flexible Iddq: 20 80 mA

Applications

- First Stage LNA for Infrastructure
- Small Cells and Cellular Repeaters
- Fast Switching TDD Systems
- General Purpose Amplifier

Product Description

The GRF2051 is a broadband, ultra-low noise linear amplifier designed for small cell, wireless infrastructure and other high performance RF applications requiring the absolute lowest possible NF, high gain and outstanding linearity. The device delivers industry leading NF and IP3 over 1700-2700 MHz using a single tune.

Configured as a first stage LNA, linear driver or cascaded gain block, GRF2051 offers high levels of reuse both within a design and across platforms. For higher gain applications from 2.3 GHz up to 3.8 GHz, the pin compatible GRF2052 should be used.

GRF2051 is housed in a 2.0 x 2.0 x 0.55 mm 12-pin plastic QFN.

Functional Block Diagram



GRF2051



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Absolute Ratings

| Parameter | Symbol | Min. | Max. | Unit |
|--|------------------|---------------|------|------|
| Supply Voltage | Vdd | 0 | 9.0 | V |
| RF Input Power: (Load VSWR < 2:1; V _D : 5.0 volts) | PIN MAX | | +20 | dBm |
| Operating Temperature (Package Heat Sink) | Тамв | -40 | +105 | °C |
| Storage Temperature | T _{STG} | -40 | +150 | °C |
| Maximum Channel Temperature (MTTF > 10^6 Hours) | Tmax | | +160 | °C |
| Maximum Disspated Power (Note: De-rate 8 mW/°C for T _{AMB} > +85C. | PDISS MAX | | 500 | mW |
| Electrostatic Discharge: | | | | |
| Charged Device Model: (TBD) | CDM | Class 4: 1000 | | V |
| Human Body Model: (TBD) | HBM | Class 1B: 500 | | V |
| Machine Model: (TBD) | MM | Class A: 50 | | V |



Caution! ESD Sensitive Device

Exceeding Absolute Maximum Rating conditions may cause permanent damage to the device.



Pin Out (Top View)



Pin Assignments

| Pin | Name | Description | Note |
|------|-----------|--------------------|--|
| 1 | GND | Ground | |
| 2 | RFin | RF Input | External match must provide DC block |
| 3 | GND | Ground | |
| 4 | GND | Ground | |
| 5 | GND | Ground | |
| 6 | GND | Ground | |
| 7 | GND | Ground | |
| 8 | RFout/Vdd | RF Output | Provide device Vdd via external bias inductor |
| 9 | GND | Ground | |
| 10 | GND | Ground | |
| 11 | GND | Ground | |
| 12 | Ven | LNA Enable Control | Venable and series resistor set Iddq. Venable < 0.4 volts disables device. |
| PKG | GND | Ground | Provides DC and RF ground for LNA, as well as thermal heat sink. |
| BASE | | | |



| Parameter | Symbol Specification | | | on | Unit | Condition | |
|--|----------------------|------|-------|------|------|--|--|
| Farameter | Symbol | Min. | Тур. | Max. | Unit | Condition | |
| Gain Mode (Venable high) | | | | | | Vdd = 5.0 V, T _A = 25 °C | |
| Test Frequency | F _{test} | | 1900 | | MHz | 1700 – 2700 MHz Tune | |
| Evaluation Board Gain | S21 | | 19.0 | | dB | | |
| Input Return Loss | S11 | | -12 | | dB | | |
| Output Return Loss | S22 | | -12 | | dB | | |
| Evaluation Board Noise Figure | NF | | 0.35 | | dB | Evaluation Board SMA to SMA | |
| De-embedded Noise Figure | NF | | 0.25 | | dB | Device Pin 2 to Pin 8 | |
| Input 3rd Order Intercept Point | IIP3 | | +20.0 | | dBm | +2 dBm P _{OUT} per tone at 2 MHz Spacing (2599 and 2601 MHz) | |
| Input 1dB Compression Point | IP1dB | | +3.0 | | dBm | | |
| Switching Rise Time | T _{RISE} | | 300 | | ns | | |
| Switching Fall Time | TFALL | | 300 | | ns | | |
| Supply Current | ldd | | 55 | | mA | Adjustable for optimal IP3 | |
| Enable Current | lenable | | 2 | | mA | | |
| Thermal Data | | | | | | | |
| Thermal Resistance (measured via IR scan) | Θјс | | 118 | | °C/W | On standard evaluation board | |
| Channel Temperature @ +85 C Reference (Package Heat Sink) | Tchannel | | +117 | | ٥C | Vdd: 5.0 V; Iddq: 55 mA; No RF; Pdiss: 275 mW | |

GRF2051 Multi-Band, Measured Performance Summary Table:

| Tune (MHz) | Reference Freg. (MHz) | Gain (dB) | Eval Board NF (dB) | De-embedded NF (dB) | OP1dB (dBm) | OIP3 (dBm) | Bias Condition (V/mA) |
|---------------|--------------------------|--------------|-----------------------|------------------------|----------------|---------------|--------------------------|
| 1700 - 2700 | 1700 | 19.8 | 0.32 | 0.25 | +20.5 | +38.0 | 5.0/55 |
| 1700 - 2700 | 1900 | 19.0 | 0.35 | 0.25 | +21.0 | +39.0 | 5.0/55 |
| 1700 - 2700 | 2300 | 17.3 | 0.43 | 0.31 | +21.5 | +42.0 | 5.0/55 |
| 1700 - 2700 | 2500 | 16.5 | 0.44 | 0.35 | +21.5 | +43.0 | 5.0/55 |
| 1700 - 2700 | 2700 | 15.8 | 0.46 | 0.36 | +21.5 | +44.5 | 5.0/55 |



GRF2051 Evaluation Board S-Parameters and Stability Mu Factor: 1700 – 2700 MHz Tune









GRF2051







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GRF2051 Theory of Operation:

The GRF2051 is a single-stage, high-performance, ultra-low noise linear amplifier that is suitable for a wide range of high performance applications. With simple external matching on the output, the device can be tuned over 700-3800 MHz with fractional bandwidths up to 30%. This device is the intermediate gain member of the GRF205X family of LNA optimized as follows:

GRF2050: Optimized for 700 – 960 MHz (In Development) GRF2051: Optimized for 1700 – 2700 MHz (Single Tune) GRF2052: Optimized for 2300 – 2700 MHz and 3300 – 3800 MHz (Separate Tunes)

The device Iddq can be set independently from the supply voltage Vdd via the bias resistor in series with Venable. This allows the device Iddq to be optimized to meet a given linearity requirement with the highest possible efficiency. For a given Venable, increasing this resistor will result in lower Iddq.







GRF2051 12-Pin QFN Package Dimensions



| Data Sheet Release Status: | Notes |
|----------------------------|---|
| Advance | S-parameter and NF data based on EM simulations for the fully packaged device |
| | using foundry supplied transistor s-parameters. Linearity estimates based on |
| | device size, bias condition and experience with related devices. |
| Preliminary | All data based on evaluation board measurements in the Guerrilla RF |
| | Applications Lab. |
| Released | All data based on device qualification data. Typically, this data is nearly identical |
| | to the data found in the preliminary version. Max and min values for key RF |
| | parameters are included. |

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